# **Quad 3-State Noninverting Buffers**

### **High-Performance Silicon-Gate CMOS**

The MC74HC125A and MC74HC126A are identical in pinout to the LS125 and LS126. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC125A and HC126A noninverting buffers are designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low (HC125A) or active-high (HC126A).

### **Features**

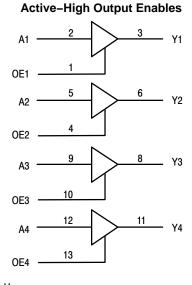
- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7 A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### **LOGIC DIAGRAM**

# A1 2 3 Y1 OE1 1 A2 5 6 Y2 OE2 4 A3 9 8 Y3 OE3 10

**HC125A** 

**Active-Low Output Enables** 



**HC126A** 

PIN 14 = V<sub>CC</sub> PIN 7 = GND



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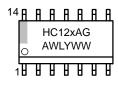


SOIC-14 NB D SUFFIX CASE 751A TSSOP-14 DT SUFFIX CASE 948G

### **PIN ASSIGNMENT**

OE1	1●	14	v <sub>cc</sub>
A1 [	2	13	0E4
Y1 [	3	12	A4
OE2	4	11	Y4
A2 [	5	10	р оез
Y2 [	6	9	_ A3
GND [	7	8	Y3
			•

### MARKING DIAGRAMS





SOIC-14 NB

TSSOP-14

26A

Output Y

> H L Z

x = 5, 6

A = Assembly Location

L, WL = Wafer Lot Y, YY = Year

W, WW = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

### **FUNCTION TABLE**

HC125A					HC1
Inputs		Output		Inp	outs
Α	OE	Υ		Α	OE
Н	L	Н		Н	Н
L	L	L		L	Н
Χ	Н	Z		Χ	L

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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OE4

### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
P <sub>D</sub>	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: –7 mW/°C from 65° to 125°C TSSOP Package: –6.1 mW/°C from 65° to 125°C

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		<b>-</b> 55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	(Figure 1) V <sub>CC</sub>	c = 2.0  V c = 4.5  V c = 6.0  V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit		mit	
			V <sub>CC</sub>	-55 to			
Symbol	Parameter	Test Conditions	v	25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$	2.0	1.5	1.5	1.5	V
		$ I_{out}  \le 20 \mu\text{A}$	3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
$V_{IL}$	Maximum Low-Level Input Voltage	V <sub>out</sub> = 0.1 V	2.0	0.5	0.5	0.5	V
		$ I_{out}  \le 20 \mu\text{A}$	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V <sub>OH</sub>	Minimum High-Level Output	$V_{in} = V_{IH}$	2.0	1.9	1.9	1.9	V
	Voltage	$ I_{out}  \le 20 \mu\text{A}$	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH}$ $ I_{out}  \le 3.6 \text{ mA}$	3.0	2.48	2.34	2.2	
		$ I_{out}  \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
		$ I_{out}  \le 7.8 \text{ mA}$	6.0	5.48	5.34	5.2	
V <sub>OL</sub>	Maximum Low-Level Output	$V_{in} = V_{IL}$	2.0	0.1	0.1	0.1	V
	Voltage	$ I_{out}  \leq 20 \mu\text{A}$	4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		$V_{in} = V_{IL}$ $ I_{out}  \le 3.6 \text{ mA}$	3.0	0.26	0.33	0.4	
		$ I_{out}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
		$ I_{out}  \le 7.8 \text{ mA}$	6.0	0.26	0.33	0.4	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μΑ
loz	Maximum Three–State Leakage	Output in High-Impedance State	6.0	±0.5	±5.0	±10	μΑ
	Current	$V_{in} = V_{IL}$ or $V_{IH}$					
		$V_{out} = V_{CC}$ or GND					
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	4.0	40	160	μΑ
	(per Package)	$I_{out} = 0 \mu A$					

### AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6.0 \text{ ns}$ )

			Guaranteed Limit			
Symbol	Parameter		–55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>PLH</sub> ,	Maximum Propagation Delay, Input A to Output Y	2.0	90	115	135	ns
$t_{PHL}$	(Figures 1 and 3)	3.0	36	45	60	
		4.5	18	23	27	
		6.0	15	20	23	
t <sub>PLZ</sub> ,	Maximum Propagation Delay, Output Enable to Y	2.0	120	150	180	ns
$t_{PHZ}$	(Figures 2 and 4)	3.0	45	60	80	
		4.5	24	30	36	
		6.0	20	26	31	
t <sub>PZL</sub> ,	Maximum Propagation Delay, Output Enable to Y	2.0	90	115	135	ns
$t_{PZH}$	(Figures 2 and 4)	3.0	36	45	60	
		4.5	18	23	27	
		6.0	15	20	23	
t <sub>TLH</sub> ,	Maximum Output Transition Time, Any Output	2.0	60	75	90	ns
$t_{THL}$	(Figures 1 and 3)	3.0	22	28	34	
		4.5	12	15	18	
		6.0	10	13	15	
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF
C <sub>out</sub>	Maximum 3-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF
			Typical @ 25°C, V <sub>CC</sub> = 5.0 V			
$C_{PD}$	Power Dissipation Capacitance (Per Buffer)*			30		pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

### **SWITCHING WAVEFORMS**

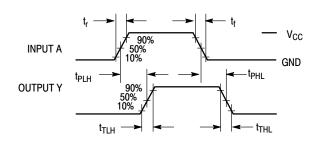


Figure 1.

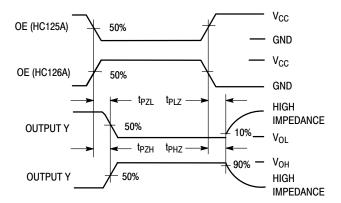
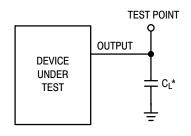


Figure 2.



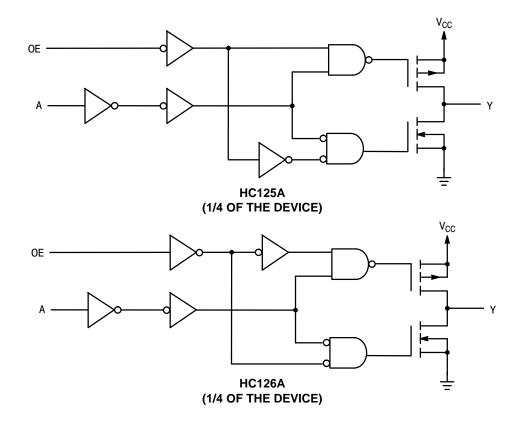
\*Includes all probe and jig capacitance

DEVICE UNDER TEST POINT  $\begin{array}{c|c} & & & & \\ &$ 

\*Includes all probe and jig capacitance

Figure 3. Test Circuit

Figure 4. Test Circuit



### **ORDERING INFORMATION**

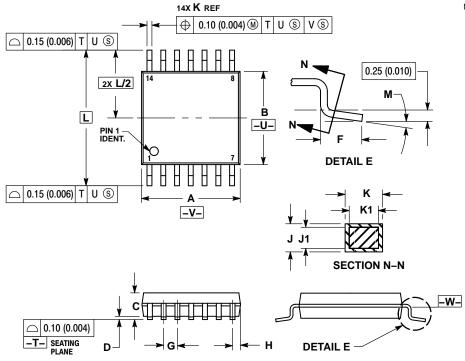
Device	Package	Shipping <sup>†</sup>
MC74HC125ADG	SOIC-14 NB (Pb-Free)	55 Units / Rail
MC74HC125ADR2G	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
MC74HC125ADTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74HC125ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC74HC126ADG	SOIC-14 NB (Pb-Free)	55 Units / Rail
MC74HC126ADR2G	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
MC74HC126ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLV74HC125ADG*	SOIC-14 NB (Pb-Free)	55 Units / Rail
NLV74HC125ADR2G*	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
NLV74HC125ADTG*	TSSOP-14 (Pb-Free)	55 Units / Rail
NLV74HC125ADTR2G*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLV74HC126ADR2G*	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
NLV74HC126ADTR2G*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

### **PACKAGE DIMENSIONS**

### TSSOP-14 CASE 948G **ISSUE B**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ANSI Y14.5M, 1982.
    2. CONTROLLING DIMENSION: MILLIMETER.
    3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
    MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

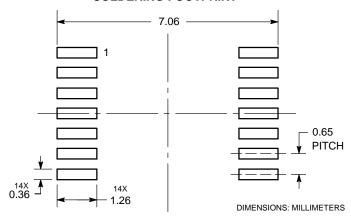
  - EXCEED 0.15 (0.006) PER SIDE.
    4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
    6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  - REFERENCE ONLY.

    7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	6.40 BSC		BSC	
М	0 °	8 °	0°	8 °	

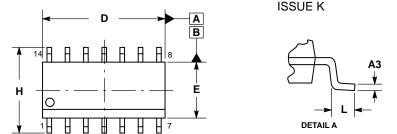
### **SOLDERING FOOTPRINT\***



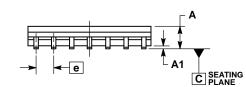
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### PACKAGE DIMENSIONS

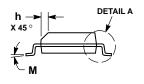
### SOIC-14 NB CASE 751A-03



⊕ 0.25 M C A S B S



| 🕁 | 0.25 (M) | B (M)



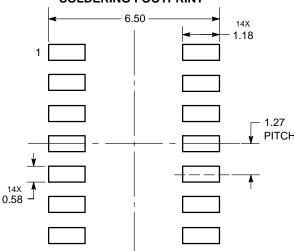
### NOTES:

- OT LO:

  1. DIMENSIONING AND TOLERANCING PER
  ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION 6 DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
м	٥°	7 °	U o	70

### **SOLDERING FOOTPRINT\***



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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